NSN 5962-01-310-7307

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delay time, high to low level

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Body Le	ngth:
0.440 inc	nes
Body Wi	dth:
0.285 inc	nes
Body He	ght:
0.085 inc	nes
Maximur	n Power Dissipation Rating:
332.8 mil	iwatts
Operatin	g Tempurature Range:
-55.0/+12	5.0 degrees celsius
Storage	Tempurature Range:
-65.0/+15	0.0 degrees celsius
Features	Provided:
Monolithi	and w/open collector and bipolar and programmable
Inclosure	Material:
Ceramic	
Inclosure	Configuration:
Flat pack	
Output L	ogic Form:
Transisto	r-transistor logic
Input Cir	cuit Pattern:
6 input	
Case Ou	line Source And Designator:
F-5 mil-m	-38510
Terminal	Surface Treatment:
Solder	
Voltage I	Rating And Type Per Characteristic:
7.0 volts	power source
Time Rat	ing Per Chacteristic:
50.00 nar	noseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay tim
output	
Memory	Device Type:
Rom	
Test Data	a Document:
96906-mi	-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
	Type And Quantity:
16 flat lea	
Shelf Life	
N/a	
Unit Of N	leasure:
Demilitar	ization:
Yes - den	

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